

RF Power Field Effect Transistors

N-Channel Enhancement-Mode Lateral MOSFETs

Designed for N-CDMA base station applications with frequencies from 1805 to 1880 MHz. Suitable for TDMA, CDMA and multicarrier amplifier applications. To be used in Class AB for PCN- PCS/cellular radio and WLL applications.

- Typical 2-Carrier N-CDMA Performance: $V_{DD} = 28$ Volts, $I_{DQ} = 1200$ mA, $P_{out} = 29$ Watts Avg., $f = 1877.5$ MHz, IS-95 CDMA (Pilot, Sync, Paging, Traffic Codes 8 Through 13) Channel Bandwidth = 1.2288 MHz. PAR = 9.8 dB @ 0.01% Probability on CCDF.
Power Gain — 16 dB
Drain Efficiency — 27.5%
IM3 @ 2.5 MHz Offset — -36 dBc in 1.2288 MHz Bandwidth
ACPR @ 885 kHz Offset — -50.5 dBc in 30 kHz Bandwidth
- Capable of Handling 10:1 VSWR, @ 28 Vdc, 1840 MHz, 140 Watts CW Output Power

Features

- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched for Ease of Use
- Qualified Up to a Maximum of 32 V_{DD} Operation
- Integrated ESD Protection
- Designed for Lower Memory Effects and Wide Instantaneous Bandwidth Applications
- RoHS Compliant
- In Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 inch Reel.

MRF6S18140HR3
MRF6S18140HSR3

1805-1880 MHz, 29 W AVG., 28 V
2 x N-CDMA
LATERAL N-CHANNEL
RF POWER MOSFETs

CASE 465B-03, STYLE 1
NI-880
MRF6S18140HR3

CASE 465C-02, STYLE 1
NI-880S
MRF6S18140HSR3

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +68	Vdc
Gate-Source Voltage	V_{GS}	-0.5, +12	Vdc
Storage Temperature Range	T_{stg}	-65 to +150	°C
Case Operating Temperature	T_C	150	°C
Operating Junction Temperature (1,2)	T_J	225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value (2,3)	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$		°C/W
Case Temperature 80°C, 140 W CW		0.31	
Case Temperature 73°C, 29 W CW		0.35	

1. Continuous use at maximum temperature will affect MTTF.
2. MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.
3. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114)	2 (Minimum)
Machine Model (per EIA/JESD22-A115)	A (Minimum)
Charge Device Model (per JESD22-C101)	IV (Minimum)

Table 4. Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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Off Characteristics

Zero Gate Voltage Drain Leakage Current ($V_{DS} = 68\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	1	μAdc
Gate-Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μAdc

On Characteristics

Gate Threshold Voltage ($V_{DS} = 10\text{ Vdc}$, $I_D = 300\text{ }\mu\text{Adc}$)	$V_{GS(th)}$	1.2	2	2.7	Vdc
Gate Quiescent Voltage ($V_{DD} = 28\text{ Vdc}$, $I_D = 1200\text{ mAdc}$, Measured in Functional Test)	$V_{GS(Q)}$	2	2.7	3.8	Vdc
Drain-Source On-Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 3\text{ Adc}$)	$V_{DS(on)}$	0.1	0.22	0.3	Vdc

Dynamic Characteristics ⁽¹⁾

Reverse Transfer Capacitance ($V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{rss}	—	2.2	—	pF
Output Capacitance ($V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{oss}	—	685	—	pF

Functional Tests (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$, $I_{DQ} = 1200\text{ mA}$, $P_{out} = 29\text{ W Avg.}$, $f_1 = 1877.5\text{ MHz}$, $f_2 = 1880\text{ MHz}$, 2-Carrier N-CDMA, 1.2288 MHz Channel Bandwidth Carriers. ACPR measured in 30 kHz Channel Bandwidth @ $\pm 885\text{ kHz}$ Offset. IM3 measured in 1.2288 MHz Channel Bandwidth @ $\pm 2.5\text{ MHz}$ Offset. PAR = 9.8 dB @ 0.01% Probability on CCDF.

Power Gain	G_{ps}	15	16	18	dB
Drain Efficiency	η_D	25.5	27.5	—	%
Intermodulation Distortion	IM3	—	-36	-34.5	dBc
Adjacent Channel Power Ratio	ACPR	—	-50.5	-48	dBc
Input Return Loss	IRL	—	-10.5	—	dB

1. Part internally matched both on input and output.

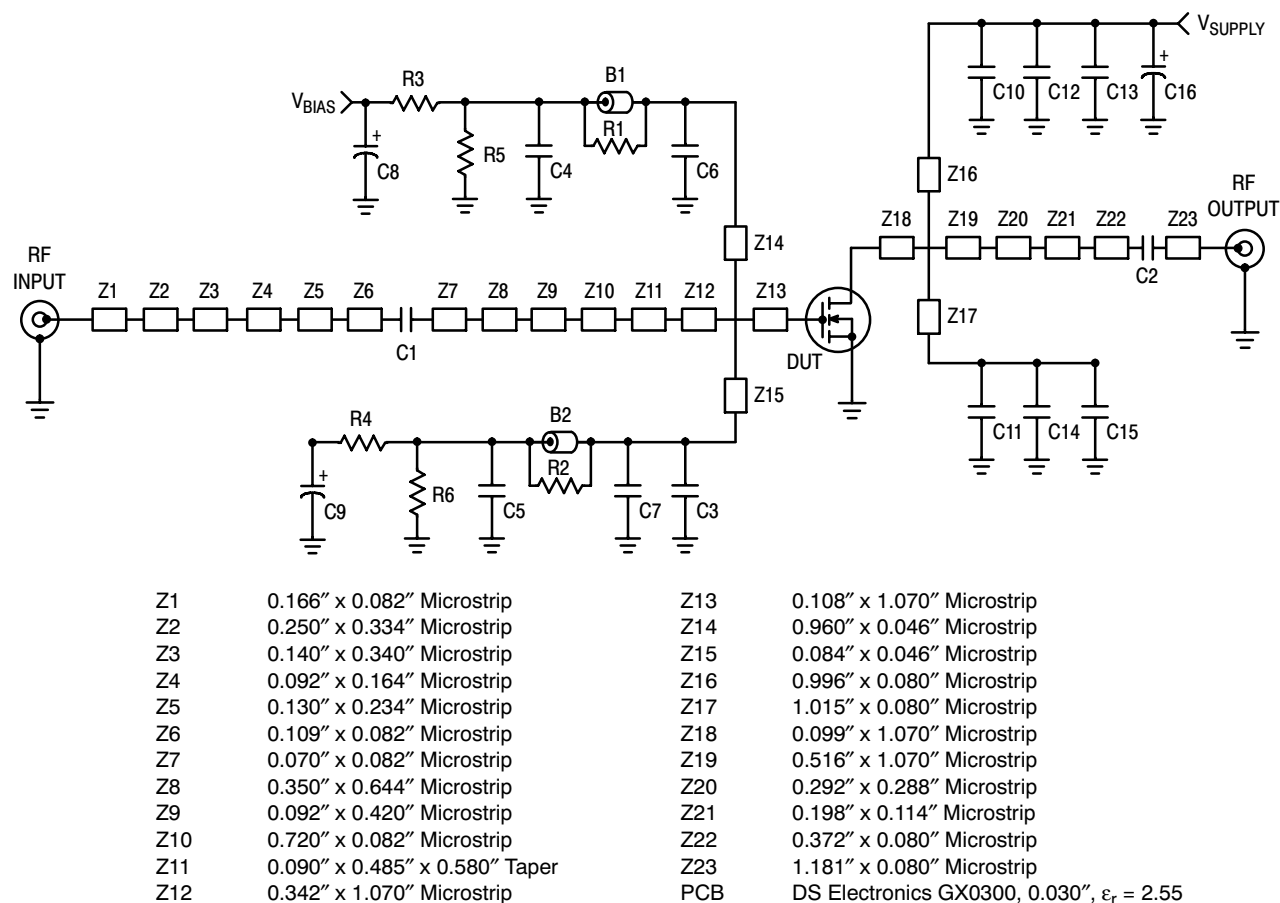


Figure 1. MRF6S18140HR3(HSR3) Test Circuit Schematic

Table 5. MRF6S18140HR3(HSR3) Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
B1, B2	47 Ω , 100 MHz Small Ferrite Beads, Surface Mount	2743019447	Fair-Rite
C1, C2	39 pF Chip Capacitors	ATC700B390FT500XT	ATC
C3	0.1 pF Chip Capacitor	ATC100B0R1BT500XT	ATC
C4, C5, C12, C13, C14, C15	10 μ F, 50 V Chip Capacitors	GRM55DR61H106KA88B	Murata
C6, C7, C10, C11	9.1 pF Chip Capacitors	ATC100B9R1BT500XT	ATC
C8, C9	47 μ F, 50 V Electrolytic Capacitors	EMVY500ADA470MF80G	Nippon Chemi-Con
C16	470 μ F, 63 V Electrolytic Capacitor	EMVY630GTR471MMH0S	Nippon Chemi-Con
R1, R2	12 Ω , 1/4 W Resistors	CRCW120612R0FKEA	Vishay
R3, R4	1.0 K Ω , 1/4 W Resistors	CRCW12061001FKEA	Vishay
R5, R6	560 K Ω , 1/4 W Chip Resistors	CRCW12065602FKEA	Vishay

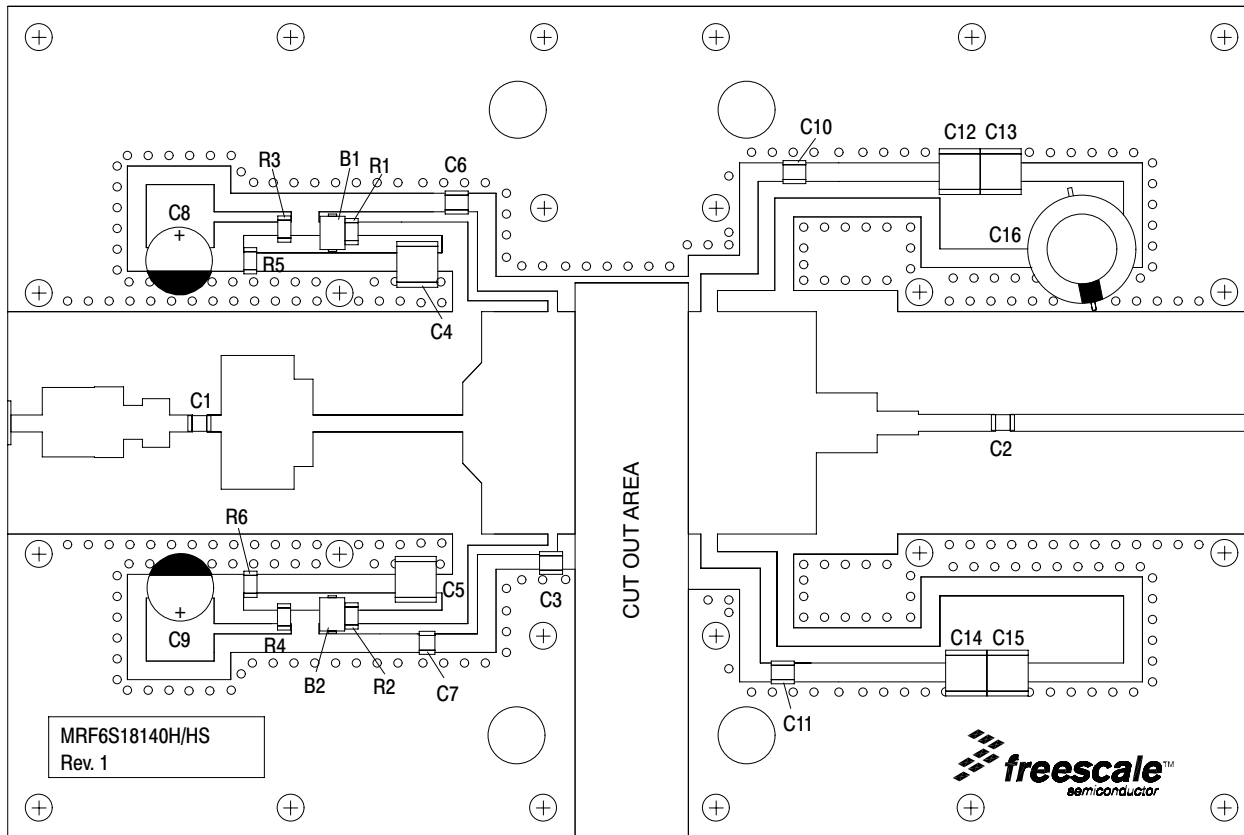


Figure 2. MRF6S18140HR3(HSR3) Test Circuit Component Layout

TYPICAL CHARACTERISTICS

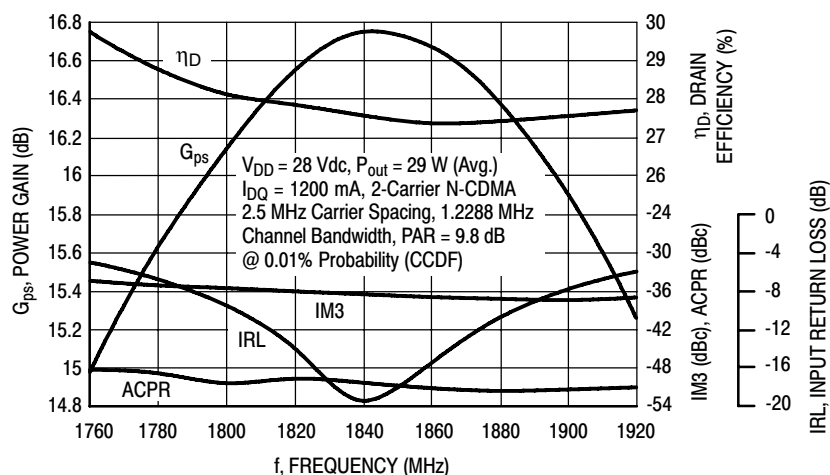


Figure 3. 2-Carrier N-CDMA Broadband Performance @ $P_{out} = 29$ Watts Avg.

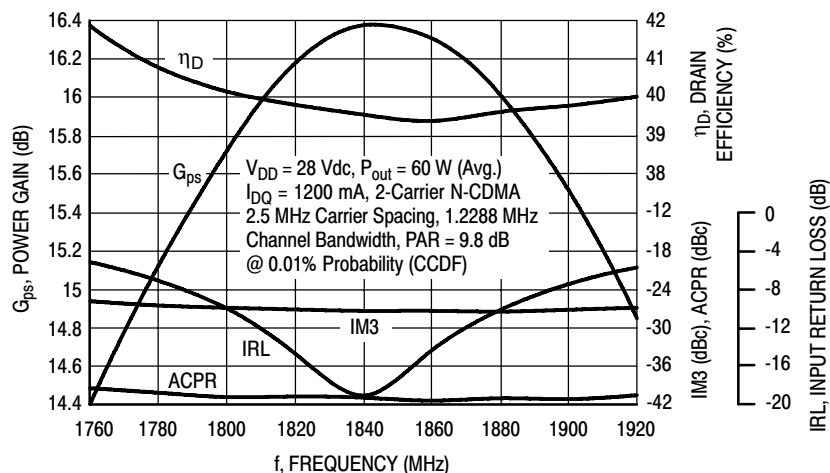


Figure 4. 2-Carrier N-CDMA Broadband Performance @ $P_{out} = 60$ Watts Avg.

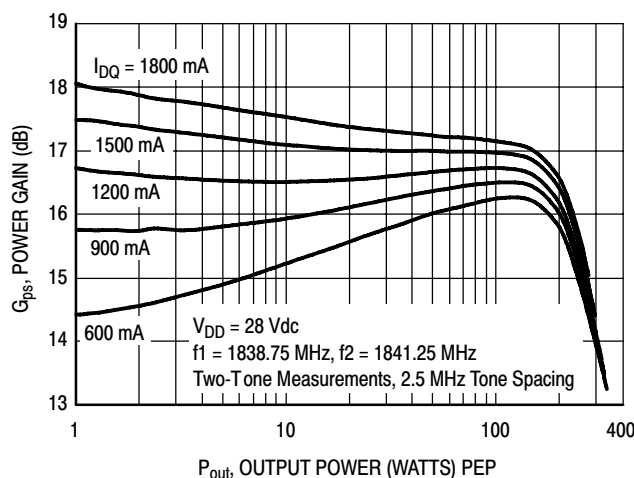


Figure 5. Two-Tone Power Gain versus Output Power

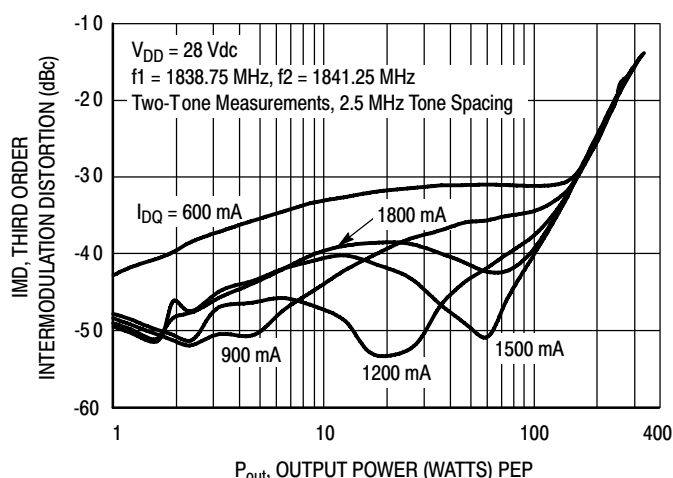


Figure 6. Third Order Intermodulation Distortion versus Output Power

TYPICAL CHARACTERISTICS

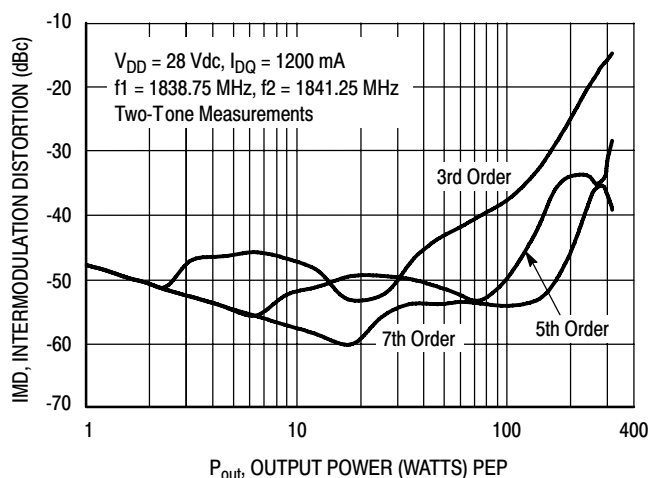


Figure 7. Intermodulation Distortion Products versus Output Power

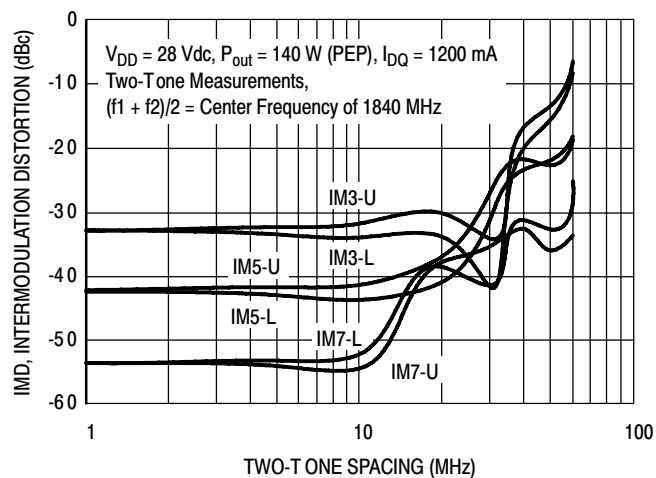


Figure 8. Intermodulation Distortion Products versus Tone Spacing

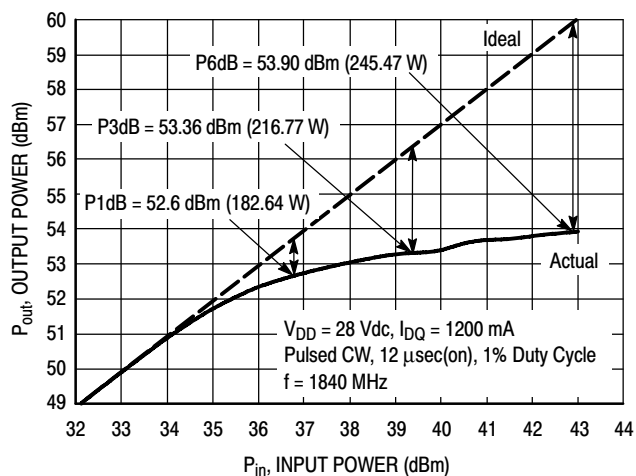


Figure 9. Pulsed CW Output Power versus Input Power

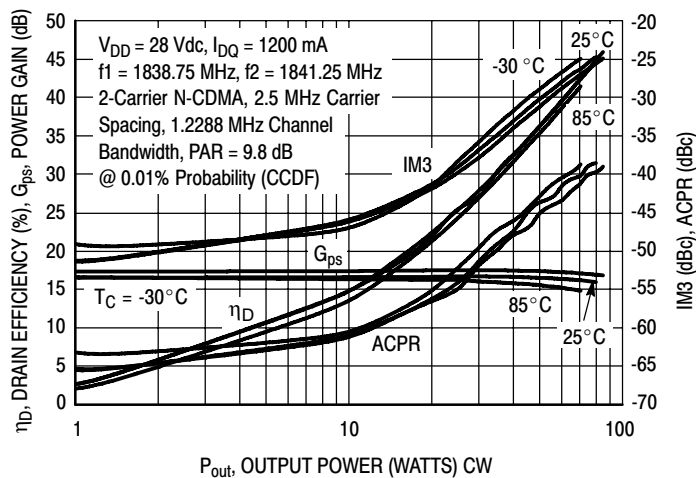


Figure 10. 2-Carrier N-CDMA ACPR, IM3, Power Gain and Drain Efficiency versus Output Power

TYPICAL CHARACTERISTICS

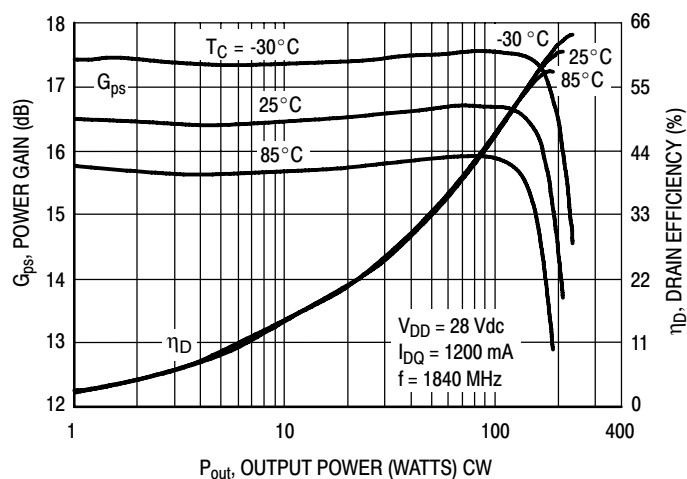


Figure 11. Power Gain and Drain Efficiency versus CW Output Power

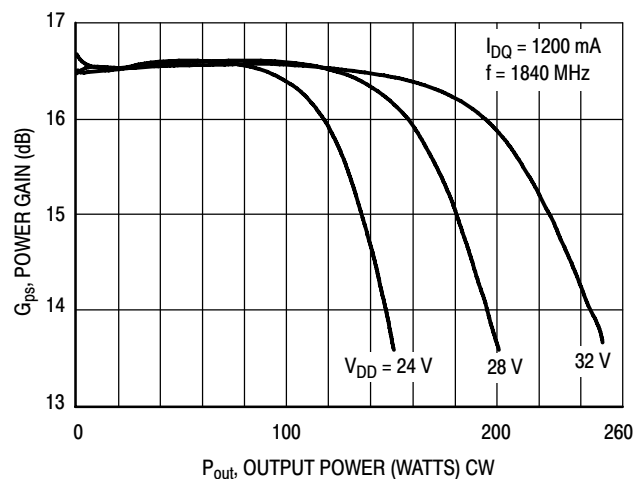
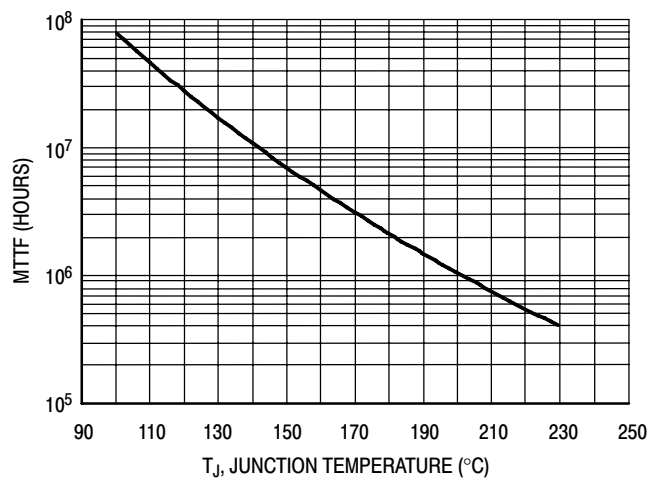


Figure 12. Power Gain versus Output Power



This above graph displays calculated MTTF in hours when the device is operated at $V_{DD} = 28$ Vdc, $P_{out} = 29$ W Avg., and $\eta_D = 27.5\%$.

MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.

Figure 13. MTTF Factor versus Junction Temperature

N-CDMA TEST SIGNAL

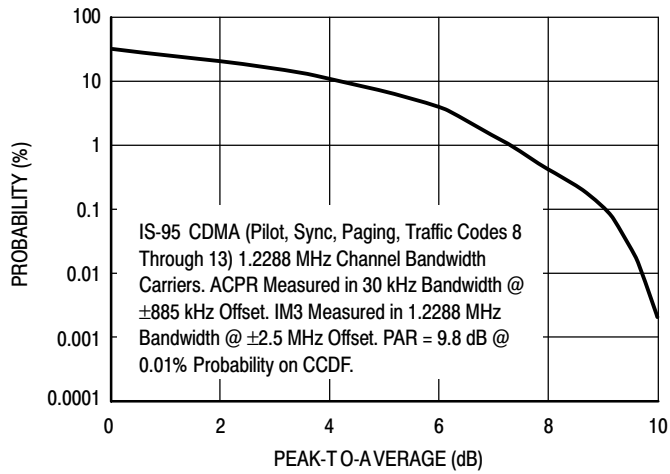


Figure 14. 2-Carrier CCDF N-CDMA

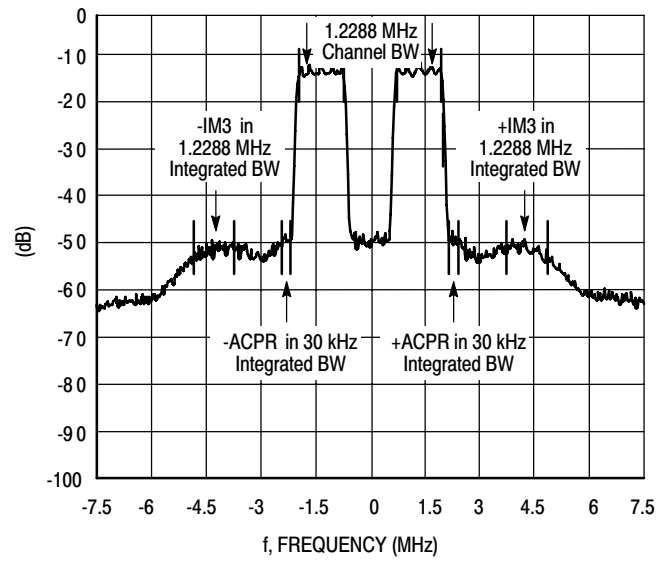
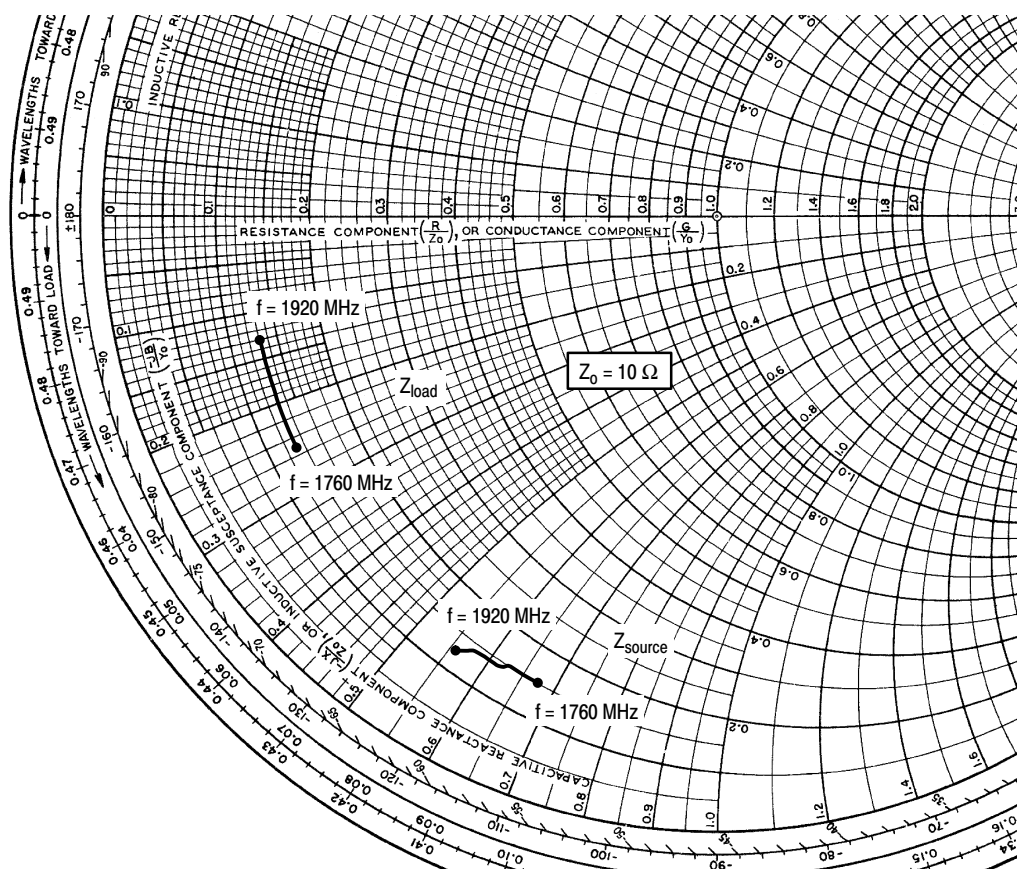


Figure 15. 2-Carrier N-CDMA Spectrum



$V_{DD} = 28 \text{ Vdc}$, $I_{DQ} = 1200 \text{ mA}$, $P_{\text{out}} = 29 \text{ W Avg.}$

f MHz	Z_{source} Ω	Z_{load} Ω
1760	1.454 - j6.703	1.344 - j2.479
1780	1.465 - j6.511	1.338 - j2.299
1800	1.467 - j6.336	1.333 - j2.129
1820	1.448 - j6.193	1.325 - j1.966
1840	1.440 - j6.049	1.308 - j1.801
1860	1.414 - j5.938	1.301 - j1.687
1880	1.377 - j5.827	1.303 - j1.550
1900	1.311 - j5.710	1.301 - j1.419
1920	1.231 - j5.583	1.289 - j1.303

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

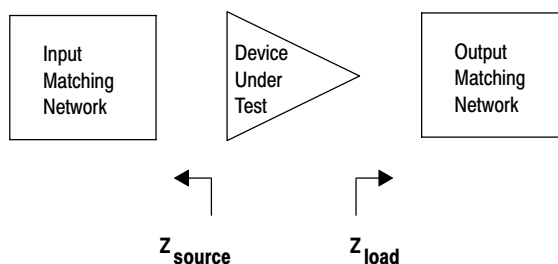
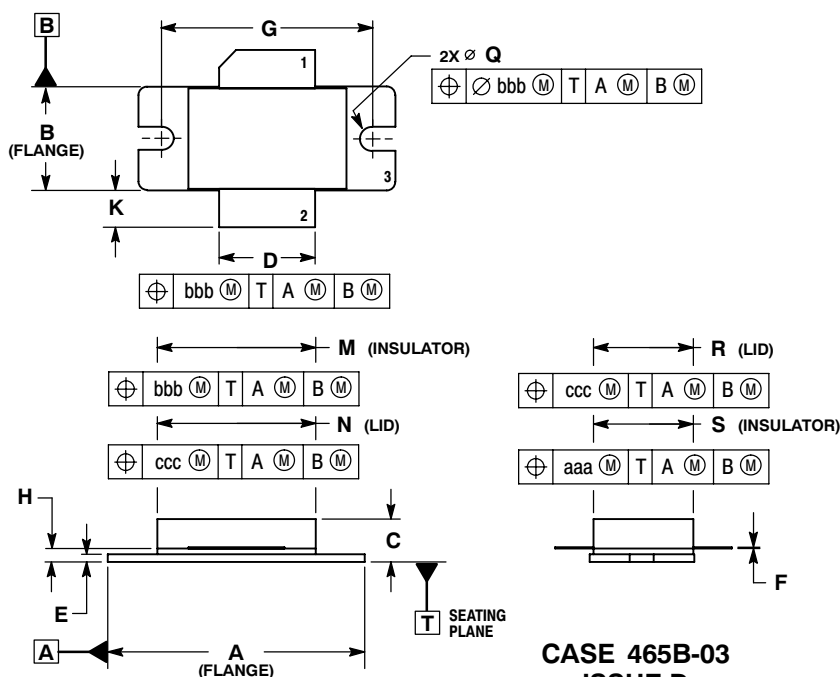


Figure 16. Series Equivalent Source and Load Impedance

MRF6S18140HR3 MRF6S18140HSR3

PACKAGE DIMENSIONS

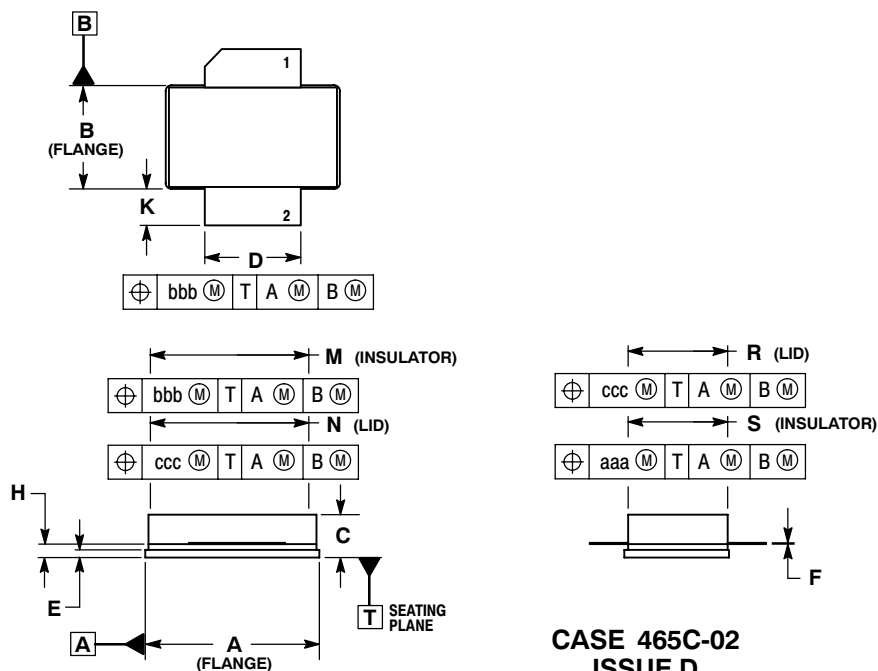


**CASE 465B-03
ISSUE D
NI-880
MRF6S18140HR3**

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.
 4. DELETED

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.335	1.345	33.91	34.16
B	0.535	0.545	13.6	13.8
C	0.147	0.200	3.73	5.08
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
G	1.100	BSC	27.94	BSC
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.872	0.888	22.15	22.55
N	0.871	0.889	19.30	22.60
Q	0.118	0.138	3.00	3.51
R	0.515	0.525	13.10	13.30
S	0.515	0.525	13.10	13.30
aaa	0.007	REF	0.178	REF
bbb	0.010	REF	0.254	REF
ccc	0.015	REF	0.381	REF

- STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE



**CASE 465C-02
ISSUE D
NI-880S
MRF6S18140HSR3**

- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.905	0.915	22.99	23.24
B	0.535	0.545	13.60	13.80
C	0.147	0.200	3.73	5.08
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.872	0.888	22.15	22.55
N	0.871	0.889	19.30	22.60
R	0.515	0.525	13.10	13.30
S	0.515	0.525	13.10	13.30
aaa	0.007	REF	0.178	REF
bbb	0.010	REF	0.254	REF
ccc	0.015	REF	0.381	REF

- STYLE 1:
PIN 1. DRAIN
2. GATE
3. SOURCE

PRODUCT DOCUMENTATION

Refer to the following documents to aid your design process.

Application Notes

- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
0	Sept. 2006	• Initial Release of Data Sheet
1	Dec. 2008	• Modified data sheet to reflect RF Test Reduction described in Product and Process Change Notification number, PCN13232, p. 1, 2 • Removed Lower Thermal Resistance and Low Gold Plating bullets from Features section as functionality is standard, p. 1 • Corrected V_{DS} to V_{DD} in the RF test condition voltage callout for $V_{GS(Q)}$, and added "Measured in Functional Test", On Characteristics table, p. 2 • Updated Part Numbers in Table 5, Component Designations and Values, to latest RoHS compliant part numbers, p. 3 • Adjusted scale for Fig. 8, Intermodulation Distortion Products versus Tone Spacing, to show wider dynamic range, p. 6 • Replaced Fig. 13, MTTF versus Junction Temperature with updated graph. Removed Amps² and listed operating characteristics and location of MTTF calculator for device, p. 7
1.1	Dec. 2009	• Corrected data sheet to reflect RF Test Reduction frequency described in Product and Process Change Notification number, PCN13232, p. 1, 2 • Data sheet archived. Part no longer manufactured.

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